

# **ISP1102A** Advanced Universal Serial Bus transceiver Rev. 01 – 15 February 2007

**Product data sheet** 

## 1. General description

The ISP1102A Universal Serial Bus (USB) transceiver is fully compliant with <u>Ref. 1</u> <u>"Universal Serial Bus Specification Rev. 2.0"</u>. The ISP1102A can transmit and receive USB data at full-speed (12 Mbit/s).

The transceiver allows USB Application-Specific Integrated Circuits (ASICs) and Programmable Logic Devices (PLDs) with power supply voltages from 1.65 V to 3.6 V to interface with the physical layer of the USB. The transceiver has an integrated 5 V-to-3.3 V voltage regulator for direct powering through USB supply line V<sub>BUS</sub>. The transceiver has an integrated voltage detector to detect the presence of the V<sub>BUS</sub> voltage (V<sub>CC(5V0)</sub>). When V<sub>CC(5V0)</sub> or VREG3V3 is lost, the DP and DM pins can be shared with other serial protocols.

The transceiver is a bidirectional differential interface and is available in HBCC16 package.

The transceiver is ideal for use in portable electronic devices, such as mobile phones, digital still cameras, Personal Digital Assistants (PDAs) and Information Appliances (IAs).

### 2. Features

- Complies with <u>Ref. 1 "Universal Serial Bus Specification Rev. 2.0"</u>
- Supports data transfer at full-speed (12 Mbit/s)
- Integrated 5 V-to-3.3 V voltage regulator to power through USB line V<sub>BUS</sub>
- V<sub>BUS</sub> voltage presence indication on pin VBUSDET
- VP and VM pins function in bidirectional mode, allowing pin count saving for the ASIC interface
- Used as USB device transceiver or USB host transceiver
- Stable RCV output during Single-Ended Zero (SE0) condition
- Two single-ended receivers with hysteresis
- Low-power operation
- Supports I/O voltage range from 1.65 V to 3.6 V
- ±12 kV ElectroStatic Discharge (ESD) protection at the DP, DM, V<sub>CC(5V0)</sub> and GND pins
- Full industrial operating temperature range from -40 °C to +85 °C
- Available in HBCC16 lead-free and halogen-free package



Advanced USB transceiver

**ISP1102A** 

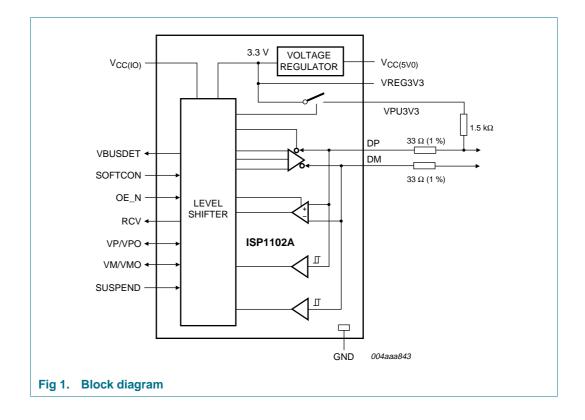
## 3. Applications

- Portable electronic devices, such as:
  - Mobile phone
  - Digital still camera
  - Personal Digital Assistant (PDA)
  - Information Appliance (IA)

## 4. Ordering information

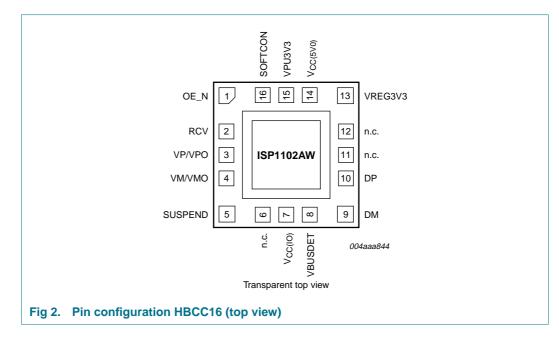
Type number	Package	Package							
	Name	Description	Version						
ISP1102AW	HBCC16	plastic thermal enhanced bottom chip carrier; 16 terminals; body $3\times3\times0.65~\text{mm}$	SOT639-2						

## 5. Block diagram



## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 2.	Pin description		
Symbol <sup>[1]</sup>	Pin	Type <sup>[2]</sup>	Description
OE_N	1	I	input for output enable (CMOS level with respect to $V_{CC(IO)},$ active LOW); enables the transceiver to transmit data on the USB bus
			input pad; push pull; CMOS
RCV	2	0	differential data receiver output (CMOS level with respect to $V_{CC(IO)}$ ); driven LOW when input SUSPEND is HIGH; the output state of RCV is preserved and stable during an SE0 condition
			output pad; push pull; 4 mA output drive; CMOS
VP/VPO	3	I/O	single-ended DP receiver output VP (CMOS level with respect to $V_{CC(IO)}$ ); for external detection of SE0, error conditions, speed of connected device; this pin also acts as drive data input VPO; see <u>Table 3</u> and <u>Table 4</u>
			bidirectional pad; push-pull input; 3-state output; 4 mA output drive; CMOS
VM/VMO	4	I/O	single-ended DM receiver output VM (CMOS level with respect to $V_{CC(IO)}$ ); for external detection of SE0, error conditions, speed of connected device; this pin also acts as drive data input VMO; see <u>Table 3</u> and <u>Table 4</u>
			bidirectional pad; push-pull input; 3-state output; 4 mA output drive; CMOS
SUSPEND	0 5	I	suspend input (CMOS level with respect to $V_{CC(IO)}$ ); a HIGH level enables low-power state while the USB bus is inactive and drives output RCV to a LOW level
			input pad; push pull; CMOS
n.c.	6	-	not connected

### **NXP Semiconductors**

Table 2.	Pin description	continued	
Symbol <sup>[1]</sup>	Pin	Type <sup>[2]</sup>	Description
V <sub>CC(IO)</sub>	7	-	supply voltage for digital I/O pins (1.65 V to 3.6 V); when V <sub>CC(IO)</sub> is not connected, the DP and DM pins are in 3-state; this supply pin is totally independent of V <sub>CC(5V0)</sub> and VREG3V3 and must never exceed the VREG3V3 voltage
VBUSDET	8	0	$V_{BUS}$ indicator output (CMOS level with respect to $V_{CC(IO)}$ )
			<ul> <li>When V<sub>BUS</sub> &gt; 4.1 V, then VBUSDET = HIGH</li> </ul>
			<ul> <li>When V<sub>BUS</sub> &lt; 3.6 V, then VBUSDET = LOW</li> </ul>
			<ul> <li>When SUSPEND = HIGH, then the VBUSDET function is invalid</li> </ul>
			Connect a 1 $\mu F$ to-10 $\mu F$ decoupling capacitor (4.7 $\mu F$ capacitor is used on the ISP1102 evaluation board)
			output pad; push pull; 4 mA output drive; CMOS
DM	9	AI/O	negative USB data bus connection (analog, differential)
DP	10	AI/O	positive USB data bus connection (analog, differential)
n.c.	11	-	not connected
n.c.	12	-	not connected
VREG3V3	13	-	internal regulator option: regulated supply voltage output (3.0 V to 3.6 V) during 5 V operation; a decoupling capacitor of at least 0.1 $\mu$ F is required
			regulator bypass option: used as a supply voltage input (3.3 V $\pm$ 10 %) for 3.3 V operation
V <sub>CC(5V0)</sub>	14	-	internal regulator option: supply voltage input (4.0 V to 5.5 V); can directly be connected to USB line $V_{\text{BUS}}$
			regulator bypass option: connect to VREG3V3
VPU3V3	15	-	pull-up supply voltage (3.3 V $\pm$ 10 %); connect an external 1.5 k $\Omega$ resistor on DP (full-speed)
			This pin function is controlled by the SOFTCON input:
			<b>SOFTCON = LOW</b> — VPU3V3 floating (high-Z); ensures zero pull-up current
			SOFTCON = HIGH — VPU3V3 = 3.3 V; internally connected to VREG3V3
SOFTCON	16	I	software controlled USB connection input; a HIGH level applies 3.3 V to pin VPU3V3, which is connected to an external 1.5 k $\Omega$ pull-up resistor; this allows USB connect or disconnect signaling to be controlled by software
			input pad; push pull; CMOS
GND	exposed die pad	-	ground supply; down bonded to the exposed die pad (heat sink); to be connected to the PCB ground

Table 2 Pin description continued

[1] Symbol names with an underscore N (for example, OE\_N) indicate active LOW signals.

 $\label{eq:loss} \begin{tabular}{ll} [2] & I = input; \ O = output; \ I/O = digital input/output; \ AI/O = analog input/output. \end{tabular}$ 

## 7. Functional description

Table 3.	Function se	election				
SUSPEND	OE_N	DP, DM	RCV	VP/VPO	VM/VMO	Function
LOW	LOW	driving or receiving	active	VPO input	VMO input	normal driving (differential receiver active)
LOW	HIGH	receiving <sup>[1]</sup>	active	VP output	VM output	receiving
HIGH	LOW	driving	inactive <sup>[2]</sup>	VPO input	VMO input	driving during suspend (differential receiver inactive)
HIGH	HIGH	high-Z <sup>[1]</sup>	inactive <sup>[2]</sup>	VP output	VM output	low-power state

### 7.1 Function selection

[1] Signal levels on the DP and DM pins are determined by other USB devices and external pull-up or pull-down resistors.

[2] In suspend mode (SUSPEND = HIGH), the differential receiver is inactive and output RCV is always LOW. The resume signaling is detected through single-ended receivers VP/VPO and VM/VMO.

### 7.2 Operating functions

Table 4.	Driving function using differential input data interface (pin OE_N = LOW)				
VM/VMO	VP/VPO	Data			
LOW	LOW	SE0			
LOW	HIGH	differential logic 1			
HIGH	LOW	differential logic 0			
HIGH	HIGH	illegal state			

#### Table 5.Receiving function (pin OE\_N = HIGH)

	0	 - ,		
DP, DM		RCV	VP/VPO	VM/VMO
Differential logic 0		LOW	LOW	HIGH
Differential logic 1		HIGH	HIGH	LOW
SE0		RCV*[1]	LOW	LOW

[1] RCV\* denotes the signal level on output RCV just before the SE0 state occurs. This level is stable during the SE0 period.

### 7.3 Power supply configurations

The ISP1102A can be used with various power supply configurations, which can be changed dynamically. Table 7 provides an overview of the power supply configurations.

Normal mode —  $V_{CC(IO)}$  is connected.  $V_{CC(5V0)}$  is connected only, or  $V_{CC(5V0)}$  and VREG3V3 are connected.

For the 5 V operation,  $V_{CC(5V0)}$  is connected to a 5 V source (4.0 V to 5.5 V). The internal voltage regulator then produces 3.3 V for USB connections.

For the 3.3 V operation, both  $V_{CC(5V0)}$  and VREG3V3 are connected to a 3.3 V source (3.0 V to 3.6 V).

 $V_{CC(IO)}$  is independently connected to a voltage source (1.65 V to 3.6 V), depending on the supply voltage of the external circuit.

**Sharing mode** — V<sub>CC(IO)</sub> is connected only, V<sub>CC(5V0)</sub> is < 3.6 V, and VREG3V3 is < 2.4 V. In this mode, the DP and DM pins are 3-stated and the ISP1102A allows external signals of up to 3.6 V to share the DP and DM lines. The internal circuits of the ISP1102A ensure that virtually no current (maximum 10  $\mu$ A) is drawn through the DP and DM lines. The power consumption through pin V<sub>CC(IO)</sub> drops to the low-power (suspended) state level.

Pins VBUSDET and RCV are driven to LOW to indicate this mode. The VBUSDET function is ignored during suspend mode of the ISP1102A.

Some hysteresis is built into the detection of VREG3V3 lost.

Remark: Sharing mode is not possible in the regulator bypass option.

Table 0. Fill States in Sharing modes	
Pin	Sharing mode
V <sub>CC(5V0)</sub>	< 3.6 V
VREG3V3	< 2.4 V
V <sub>CC(IO)</sub>	1.65 V to 3.6 V input
VPU3V3	high-Z (off)
DP, DM	high-Z
VP/VPO, VM/VMO <sup>[1]</sup>	LOW
RCV	LOW
VBUSDET	LOW
OE_N, SUSPEND, SOFTCON	high-Z

#### Table 6. Pin states in sharing modes

[1] VP/VPO and VM/VMO are bidirectional pins.

#### Table 7.Power supply configuration overview

V <sub>CC(5V0)</sub>	V <sub>CC(IO)</sub>	Configuration	Special characteristics
Connected	connected	normal mode	-
< 3.6 V	connected	sharing mode	DP, DM and VPU3V3: high-Z VP/VPO and VM/VMO: driven LOW RCV: driven LOW VBUSDET: driven LOW

### 7.4 Power supply input options

The ISP1102A has two power supply input options.

**Internal regulator** — Pin  $V_{CC(5V0)}$  is connected to 4.0 V to 5.5 V. The internal regulator is used to supply the internal circuitry with 3.3 V (nominal). The VREG3V3 pin becomes a 3.3 V output reference.

**Regulator bypass** — Pins  $V_{CC(5V0)}$  and VREG3V3 are connected to the same supply. The internal regulator is bypassed and the internal circuitry is supplied directly from pin VREG3V3. The voltage range is 3.0 V to 3.6 V to comply with <u>Ref. 1 "Universal Serial</u> Bus Specification Rev. 2.0".

The supply voltage range for each input option is specified in Table 8.

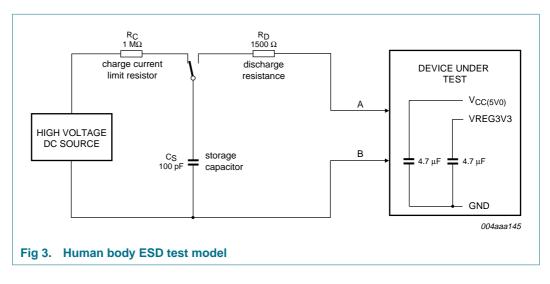
Input option	V <sub>CC(5V0)</sub>	VREG3V3	V <sub>CC(IO)</sub>
Internal regulator	supply input for internal regulator (4.0 V to 5.5 V)	voltage reference output (3.3 V, 300 μA)	supply input for digital I/O pins (1.65 V to 3.6 V)
Regulator bypass	connected to VREG3V3 with maximum voltage drop of 0.3 V (2.7 V to 3.6 V)	supply input (3.0 V to 3.6 V)	supply input for digital I/O pins (1.65 V to 3.6 V)

#### Table 8. Power supply input options

## 8. ElectroStatic Discharge (ESD)

### 8.1 ESD protection

For the HBCC package, the pins that are connected to the USB connector (DP, DM,  $V_{CC(5V0)}$  and GND) have a minimum of ±12 kV ESD protection. The ±12 kV measurement is limited by the test equipment. Capacitors of 4.7  $\mu$ F connected from VREG3V3 to GND and  $V_{CC(5V0)}$  to GND are required to achieve this ±12 kV ESD protection (see Figure 3).



### 8.2 ESD test conditions

A detailed report on test set up and results is available on request.

## 9. Limiting values

#### Table 9. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC(5V0)</sub>	supply voltage (5.0 V)		-0.5	+6.0	V
V <sub>CC(IO)</sub>	IO supply voltage		-0.5	+4.6	V
VI	input voltage		-0.5	$V_{CC(IO)}$ + 0.5 V	V
l <sub>lu</sub>	latch-up current	$V_1 = -1.8 \text{ V to } +5.4 \text{ V}$	-	100	mA
V <sub>esd</sub>	electrostatic discharge voltage	pins DP, DM, $V_{CC(5V0)}$ and GND; $I_{LI}$ < 3 $\mu A$	[1][2] -12000	+12000	V
		all other pins; $I_{LI} < 1 \ \mu A$	2 -2000	+2000	V
T <sub>stg</sub>	storage temperature		-40	+125	°C

[1] Testing equipment limits measurement to only ±12 kV. Capacitors needed on V<sub>CC(5V0)</sub> and VREG3V3 (see Section 8).

[2] Equivalent to discharging a 100 pF capacitor through a 1.5 kΩ resistor (Human Body Model).

## 10. Recommended operating conditions

#### Table 10. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC(5V0)</sub>	supply voltage (5.0 V)		4.0	5.0	5.5	V
V <sub>CC(IO)</sub>	IO supply voltage		1.65	-	3.6	V
VI	input voltage		0	-	V <sub>CC(IO)</sub>	V
V <sub>IA(I/O)</sub>	input voltage on analog I/O pins	on pins DP and DM	0	-	3.6	V
Tj	junction temperature		-40	-	+125	°C
T <sub>amb</sub>	ambient temperature		-40	-	+85	°C

### **11. Static characteristics**

#### Table 11. Static characteristics: supply pins

 $V_{CC(5V0)} = 4.0 \text{ V}$  to 5.5 V or  $V_{(VREG3V3)} = 3.0 \text{ V}$  to 3.6 V;  $V_{CC(IO)} = 1.65 \text{ V}$  to 3.6 V;  $V_{GND} = 0 \text{ V}$ ; see <u>Table 8</u> for valid voltage level combinations;  $T_{amb} = -40 \text{ }^{\circ}\text{C}$  to +85 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(VREG3V3)</sub>	voltage on pin VREG3V3	internal regulator option; $I_{load} \le 300 \ \mu A$	[1][2] 3.0	3.3	3.6	V
I <sub>CC</sub>	supply current	transmitting and receiving at 12 Mbit/s; $C_L$ = 50 pF on pins DP and DM	<u>[3]</u> _	4	8	mA
I <sub>CC(IO)</sub>	supply current on pin $V_{CC(\text{IO})}$	transmitting and receiving at 12 Mbit/s	<u>[3]</u> _	1	2	mA
I <sub>CC(idle)</sub>	idle and SE0 supply current	idle: $V_{DP}$ > 2.7 V, $V_{DM}$ < 0.3 V; SE0: $V_{DP}$ < 0.3 V, $V_{DM}$ < 0.3 V	<u>[4]</u> _	-	300	μΑ
I <sub>CC(IO)static</sub>	static supply current on pin V <sub>CC(IO)</sub>	idle, SE0 or suspend	-	-	20	μA
I <sub>CC(susp)</sub>	suspend supply current	SUSPEND = HIGH	<u>[4]</u> _	-	20	μΑ

Product data sheet

#### Table 11. Static characteristics: supply pins ...continued

 $V_{CC(5V0)} = 4.0 \text{ V}$  to 5.5 V or  $V_{(VREG3V3)} = 3.0 \text{ V}$  to 3.6 V;  $V_{CC(IO)} = 1.65 \text{ V}$  to 3.6 V;  $V_{GND} = 0 \text{ V}$ ; see <u>Table 8</u> for valid voltage level combinations;  $T_{amb} = -40 \text{ °C}$  to +85 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CC(IO)sharing</sub>	sharing mode supply current on pin $V_{CC(IO)}$	V <sub>CC(5V0)</sub> < 3.6 V	-	-	20	μΑ
Iload(sharing)DM	sharing mode load current on pin DM	$V_{CC(5V0)}$ < 3.6 V; SOFTCON = LOW; $V_{DM}$ = 3.6 V	-	-	10	μΑ
Iload(sharing)DP	sharing mode load current on pin DP	V <sub>CC(5V0)</sub> < 3.6 V; SOFTCON = LOW; V <sub>DP</sub> = 3.6 V	-	-	10	μΑ
V <sub>CC(5V0)th</sub>	supply voltage detection	$1.65~V \leq V_{CC(IO)} \leq 3.6~V$				
	threshold (5.0 V)	supply lost	-	-	3.6	V
		supply present	4.1	-	-	V
$V_{CC(5V0)hys}$	supply voltage detection hysteresis (5.0 V)	V <sub>CC(IO)</sub> = 1.8 V	-	70	-	mV
V <sub>CC(IO)th</sub>	supply voltage detection	$V_{(VREG3V3)} = 2.7 V \text{ to } 3.6 V$				
	threshold on pin $V_{CC(IO)}$	supply lost	-	-	0.5	V
		supply present	1.4	-	-	V
$V_{CC(IO)hys}$	supply voltage detection hysteresis on pin $V_{CC(IO)}$	V <sub>(VREG3V3)</sub> = 3.3 V	-	0.45	-	V
$V_{REG(3V3)th}$	regulated supply voltage detection threshold (3.3 V)	$\begin{array}{l} 1.65 \ V \leq V_{CC(IO)} \leq V_{(VREG3V3)}; \\ 2.7 \ V \leq V_{(VREG3V3)} \leq 3.6 \ V \end{array}$				
		supply lost	-	-	0.8	V
		supply present	5 2.4	-	-	V
$V_{REG(3V3)hys}$	regulated supply voltage detection hysteresis (3.3 V)	V <sub>CC(IO)</sub> = 1.8 V	-	0.45	-	V

[1]  $I_{load}$  includes the pull-up resistor current through pin VPU3V3.

[2] The minimum voltage is 2.7 V in suspend mode.

[3] Maximum value characterized only, not tested in production.

[4] Excluding any load current and VPU3V3 or V<sub>SW</sub> source current to the 1.5 kΩ and 15 kΩ pull-up and pull-down resistors (200 μA typ.).

[5] When  $V_{CC(IO)} < 2.7$  V, the minimum value for  $V_{REG(3V3)th} = 2.0$  V for supply present condition.

#### Table 12. Static characteristics: digital pins

 $V_{CC(IO)}$  = 1.65 V to 3.6 V;  $V_{GND}$  = 0 V;  $T_{amb}$  = -40 °C to +85 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC(IO)} = 1.6$	5 V to 3.6 V					
Input levels						
V <sub>IL</sub>	LOW-level input voltage		-	-	$0.3V_{CC(IO)}$	V
V <sub>IH</sub>	HIGH-level input voltage		$0.6V_{CC(IO)}$	-	-	V
Output levels	6					
V <sub>OL</sub>	LOW-level output voltage	$I_{OL} = 100 \ \mu A$	-	-	0.15	V
		$I_{OL} = 2 \text{ mA}$	-	-	0.4	V
V <sub>OH</sub>	HIGH-level output voltage	I <sub>OH</sub> = 100 μA	$V_{CC(IO)} - 0.15 \text{ V}$	-	-	V
		$I_{OH} = 2 \text{ mA}$	$V_{CC(IO)} - 0.4 V$	-	-	V

**Advanced USB transceiver** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Capacitar	nce					
C <sub>in</sub>	input capacitance	pin to GND	-	-	10	pF
Example	1: $V_{CC(IO)}$ = 1.8 V $\pm$ 0.15 V					
Input level	S					
V <sub>IL</sub>	LOW-level input voltage		-	-	0.5	V
V <sub>IH</sub>	HIGH-level input voltage		1.2	-	-	V
Output lev	rels					
V <sub>OL</sub>	LOW-level output voltage	I <sub>OL</sub> = 100 μA	-	-	0.15	V
		$I_{OL} = 2 \text{ mA}$	-	-	0.4	V
V <sub>OH</sub>	HIGH-level output voltage	I <sub>OH</sub> = 100 μA	1.5	-	-	V
		$I_{OH} = 2 \text{ mA}$	1.25	-	-	V
Leakage o	current					
ILI	input leakage current		<u>[1]</u> –1	-	+1	μA
Example	2: $V_{CC(IO)}$ = 2.5 V ± 0.2 V					
Input level	S					
V <sub>IL</sub>	LOW-level input voltage		-	-	0.7	V
V <sub>IH</sub>	HIGH-level input voltage		1.7	-	-	V
Output lev	rels					
V <sub>OL</sub>	LOW-level output voltage	I <sub>OL</sub> = 100 μA	-	-	0.15	V
		$I_{OL} = 2 \text{ mA}$	-	-	0.4	V
V <sub>OH</sub>	HIGH-level output voltage	I <sub>OH</sub> = 100 μA	2.15	-	-	V
		$I_{OH} = 2 \text{ mA}$	1.9	-	-	V
Leakage o	current					
ILI	input leakage current		<u>[1]</u> –5	-	+5	μA
Example	3: V <sub>CC(IO)</sub> = 3.3 V ± 0.3 V					
Input level	S					
V <sub>IL</sub>	LOW-level input voltage		-	-	0.9	V
VIH	HIGH-level input voltage		2.15	-	-	V
Output lev	rels					
V <sub>OL</sub>	LOW-level output voltage	$I_{OL} = 100 \ \mu A$	-	-	0.15	V
		$I_{OL} = 2 \text{ mA}$	-	-	0.4	V
V <sub>он</sub>	HIGH-level output voltage	I <sub>OH</sub> = 100 μA	2.85	-	-	V
		$I_{OH} = 2 \text{ mA}$	2.6	-	-	V
Leakage o	current					
ILI	input leakage current		<u>[1]</u> –5	-	+5	μΑ

## **Table 12.** Static characteristics: digital pins ...continued $V_{1} = 0$ $V_{1} = 0$ $V_{2} = 0$ $V_$

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[1] If  $V_{CC(IO)} \ge V_{(VREG3V3)}$ , then the leakage current will be higher than the specified value.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Input levels	;						
Differential r	eceiver						
V <sub>DI</sub>	differential input sensitivity	$ V_{DP} - V_{DM} $		0.2	-	-	V
V <sub>CM</sub>	differential common mode voltage	includes $V_{DI}$ range		0.8	-	2.5	V
Single-ende	d receiver						
V <sub>IL</sub>	LOW-level input voltage			-	-	0.8	V
V <sub>IH</sub>	HIGH-level input voltage			2.0	-	-	V
V <sub>hys</sub>	hysteresis voltage			0.4	-	0.7	V
Output leve	ls						
V <sub>OL</sub>	LOW-level output voltage	$R_L$ = 1.5 k $\Omega$ to 3.6 V		-	-	0.3	V
V <sub>OH</sub>	HIGH-level output voltage	$R_L = 15 \text{ k}\Omega \text{ to GND}$	[1]	2.8	-	3.6	V
Leakage cu	rrent						
I <sub>LZ</sub>	off-state leakage current			-1	-	+1	μA
Capacitanc	e						
C <sub>in</sub>	input capacitance	pin to GND		-	-	20	pF
Resistance							
Z <sub>DRV</sub>	driver output impedance	steady-state drive	[2]	34	39	44	Ω
Z <sub>INP</sub>	input impedance			10	-	-	MΩ
R <sub>sw(VPU3V3)</sub>	switch-on resistance on pin VPU3V3			-	-	10	Ω
Terminatio	ı						
V <sub>TERM</sub>	termination voltage	for upstream port pull-up (R <sub>PU</sub> )	[3][4]	3.0	-	3.6	V

#### Table 13. Static characteristics: analog I/O pins DP and DM

[1]  $V_{OH(min)} = V_{(VREG3V3)} - 0.2 V.$ 

[2] Includes external resistors of 33  $\Omega\pm$  1 % on both pins DP and DM.

[3] This voltage is available at pins VREG3V3 and VPU3V3.

[4] The minimum voltage is 2.7 V in suspend mode.

## **12. Dynamic characteristics**

#### Table 14. Dynamic characteristics: analog I/O pins DP and DM

 $V_{CC(5V0)} = 4.0$  V to 5.5 V or  $V_{(VREG3V3)} = 3.0$  V to 3.6 V;  $V_{CC(IO)} = 1.65$  V to 3.6 V;  $V_{GND} = 0$  V; see <u>Table 8</u> for valid voltage level combinations;  $T_{amb} = -40$  °C to +85 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Driver chara	cteristics					
t <sub>FR</sub>	rise time	$C_L$ = 50 pF to 125 pF; 10 % to 90 % of  V <sub>OH</sub> – V <sub>OL</sub>  ; see Figure 4	4	-	20	ns
t <sub>FF</sub>	fall time	$C_L$ = 50 pF to 125 pF; 90 % to 10 % of  V <sub>OH</sub> – V <sub>OL</sub>  ; see <u>Figure 4</u>	4	-	20	ns
FRFM	differential rise time/fall time matching	excluding the first transition from Idle state	90	-	111.1	%

#### Table 14. Dynamic characteristics: analog I/O pins DP and DM ...continued

 $V_{CC(5V0)} = 4.0 \text{ V}$  to 5.5 V or  $V_{(VREG3V3)} = 3.0 \text{ V}$  to 3.6 V;  $V_{CC(IO)} = 1.65 \text{ V}$  to 3.6 V;  $V_{GND} = 0 \text{ V}$ ; see <u>Table 8</u> for valid voltage level combinations;  $T_{amb} = -40 \text{ °C}$  to +85 °C; unless otherwise specified.

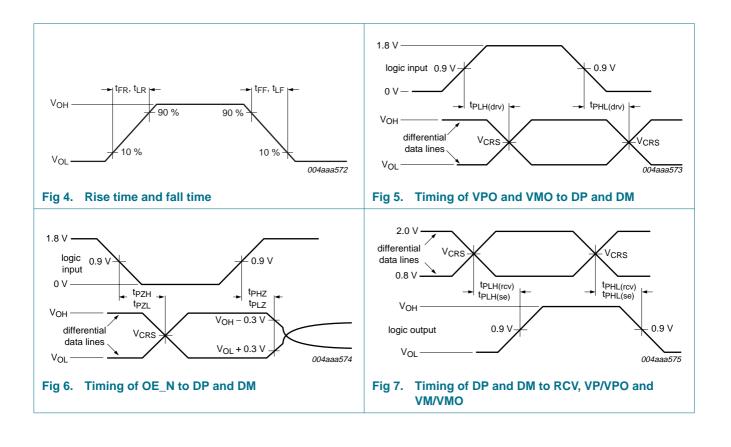
Parameter	Conditions		Min	Тур	Max	Unit
output signal crossover voltage	excluding the first transition from idle state; see $Figure 5$	<u>[1]</u>	1.3	-	2.0	V
]						
driver propagation delay (LOW to HIGH)	VPO, VMO to DP, DM; see Figure 5 and Figure 8		-	-	18	ns
driver propagation delay (HIGH to LOW)	VPO, VMO to DP, DM; see Figure 5 and Figure 8		-	-	18	ns
driver disable delay from HIGH level	OE_N to DP, DM; see <u>Figure 6</u> and <u>Figure 9</u>		-	-	15	ns
driver disable delay from LOW level	OE_N to DP, DM; see <u>Figure 6</u> and <u>Figure 9</u>		-	-	15	ns
driver enable delay to HIGH level	OE_N to DP, DM; see Figure 6 and Figure 9		-	-	15	ns
driver enable delay to LOW level	OE_N to DP, DM; see <u>Figure 6</u> and <u>Figure 9</u>		-	-	15	ns
ings						
ceiver						
receiver propagation delay (LOW to HIGH)	DP, DM to RCV; see Figure 7 and Figure 10		-	-	15	ns
receiver propagation delay (HIGH to LOW)	DP, DM to RCV; see Figure 7 and Figure 10		-	-	15	ns
receiver						
single-ended propagation delay (LOW to HIGH)	DP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10		-	-	18	ns
single-ended propagation delay (HIGH to LOW)	DP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10		-	-	18	ns
	output signal crossover         voltage         driver propagation         delay (LOW to HIGH)         driver propagation         delay (HIGH to LOW)         driver disable delay         from HIGH level         driver enable delay to         HIGH level         driver enable delay to         HIGH level         driver enable delay to         LOW level         ings         ceiver         receiver propagation         delay (LOW to HIGH)         receiver propagation         delay (HIGH to LOW)         receiver propagation         delay (LOW to HIGH)         single-ended         propagation delay         (LOW to HIGH)         single-ended         propagation delay	output signal crossover voltageexcluding the first transition from idle state; see Figure 5output signal crossover voltageexcluding the first transition from idle state; see Figure 5driver propagation delay (LOW to HIGH)VPO, VMO to DP, DM; see Figure 5 and Figure 8driver propagation delay (HIGH to LOW)VPO, VMO to DP, DM; see Figure 5 and Figure 8driver disable delay from HIGH levelOE_N to DP, DM; see Figure 6 and Figure 9driver disable delay from LOW levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to HIGH levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to LOW levelOE_N to DP, DM; see Figure 7 and Figure 9ingsCeiverreceiver propagation delay (LOW to HIGH)DP, DM to RCV; see Figure 7 and Figure 10receiverDP, DM to VP/VPO, VM/VMO; see Figure 10single-ended propagation delay (LOW to HIGH)DP, DM to VP/VPO, VM/VMO; see Figure 10single-ended propagation delayDP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10	output signal crossover voltageexcluding the first transition from idle state; see Figure 5[1]driver propagation delay (LOW to HIGH)VPO, VMO to DP, DM; see Figure 5 and Figure 8driver propagation delay (HIGH to LOW)VPO, VMO to DP, DM; see Figure 5 and Figure 8driver disable delay from HIGH levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to HIGH levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9driver enable delay to LOW levelOE_N to DP, DM; see Figure 7 and Figure 10receiverPP, DM to RCV; see Figure 7 and Figure 10receiver propagation delay (HIGH to LOW)DP, DM to RCV; see Figure 7 and Figure 10receiverDP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10single-ended propagation delay (LOW to HIGH)DP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10	output signal crossover voltageexcluding the first transition from idle state; see Figure 511driver propagation delay (LOW to HIGH)VPO, VMO to DP, DM; see Figure 5 and Figure 8-driver propagation delay (HIGH to LOW)VPO, VMO to DP, DM; see Figure 5 and Figure 8-driver disable delay from HIGH levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay from LOW levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay to LOW levelOE_N to DP, DM; see Figure 6 and Figure 9-driver enable delay to LOW levelOE_N to DP, DM; see Figure 7 and Figure 10-receiver propagation delay (LOW to HIGH)DP, DM to RCV; see Figure 7 and Figure 10-receiverSingle-ended propagation delay (LOW to HIGH)DP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10-single-ended propagation delay (LOW to HIGH)DP, DM to VP/VPO, VM/VMO; see Figure 7 and Figure 10-	output signal crossover voltageexcluding the first transition from idle state; see Figure 511 1.3-driver propagation delay (LOW to HIGH)VPO, VMO to DP, DM; see Figure 5 and Figure 8driver propagation delay (HIGH to LOW)VPO, VMO to DP, DM; see Figure 5 and Figure 8driver disable delay from HIGH levelOE_N to DP, DM; see Figure 6 and Figure 9driver disable delay from LOW levelOE_N to DP, DM; 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[1] Characterized only, not tested. Limits guaranteed by design.

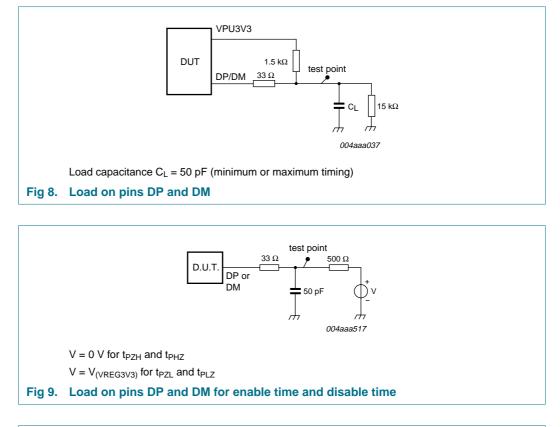
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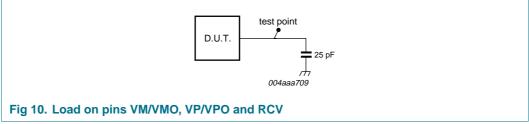
### Advanced USB transceiver

**ISP1102A** 



## 13. Test information

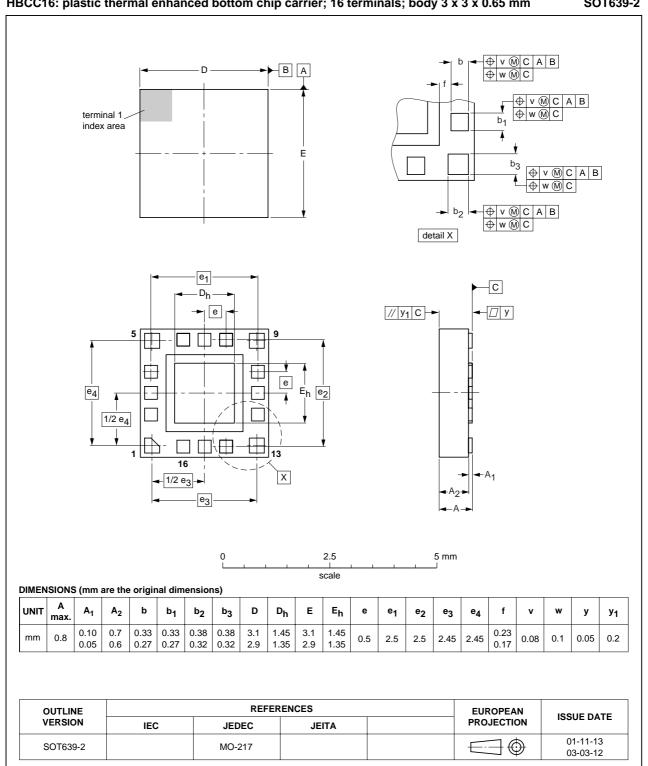




ISP1102A\_1 Product data sheet

**ISP1102A** Advanced USB transceiver

## 14. Package outline



HBCC16: plastic thermal enhanced bottom chip carrier; 16 terminals; body 3 x 3 x 0.65 mm

SOT639-2

Fig 11. Package outline SOT639-2 (HBCC16) ISP1102A 1

### **15. Packing information**

The ISP1102AW (HBCC16 package) is delivered on a Type A carrier tape, see <u>Figure 12</u>. The tape dimensions are given in <u>Table 15</u>.

The reel diameter is 330 mm. The reel is made of polystyrene (PS) and is not designed for use in a baking process.

The cumulative tolerance of 10 successive sprocket holes is  $\pm 0.02$  mm. The camber must not exceed 1 mm in 100 mm.

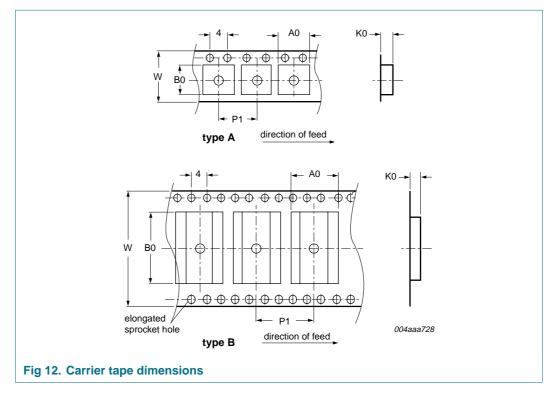


 Table 15.
 Type A carrier tape dimensions for the ISP1102AW

Dimension	Value	Unit
A0	3.3	mm
В0	3.3	mm
К0	1.1	mm
P1	8.0	mm
W	$12.0\pm0.3$	mm

## 16. Soldering

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

### 16.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

### 16.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- · Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus PbSn soldering

### 16.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

### 16.4 Reflow soldering

Key characteristics in reflow soldering are:

 Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see <u>Figure 13</u>) than a PbSn process, thus reducing the process window

- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 16 and 17

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm <sup>3</sup> )		
	< 350	≥ 350	
< 2.5	235	220	
≥ 2.5	220	220	

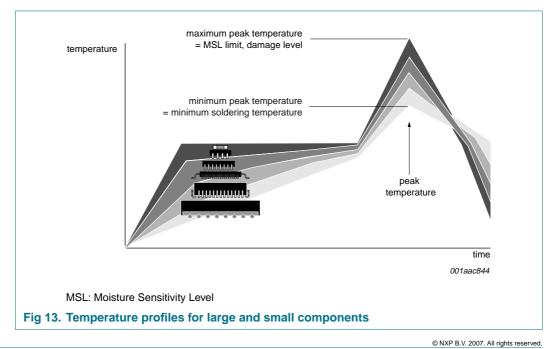
#### Table 16. SnPb eutectic process (from J-STD-020C)

#### Table 17. Lead-free process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)				
	Volume (mm <sup>3</sup> )				
	< 350	350 to 2000	> 2000		
< 1.6	260	260	260		
1.6 to 2.5	260	250	245		
> 2.5	250	245	245		

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 13.



For further information on temperature profiles, refer to Application Note *AN10365 "Surface mount reflow soldering description"*.

## **17. Abbreviations**

Table 18.	Abbreviations
Acronym	Description
ASIC	Application-Specific Integrated Circuit
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
SE0	Single-Ended Zero
USB	Universal Serial Bus

### **18. References**

- [1] Universal Serial Bus Specification Rev. 2.0
- [2] Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM) (JESD22-A114D)

## **19. Revision history**

### Table 19.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ISP1102A_1	20070215	Product data sheet	-	-

## **20. Legal information**

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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 22. Tables

Table 1.	Ordering information2
Table 2.	Pin description
Table 3.	Function selection
Table 4.	Driving function using differential input data
	interface (pin OE_N = LOW)5
Table 5.	Receiving function (pin OE_N = HIGH)5
Table 6.	Pin states in sharing modes
Table 7.	Power supply configuration overview
Table 8.	Power supply input options
Table 9.	Limiting values
Table 10.	Recommended operating conditions
Table 11.	Static characteristics: supply pins9
Table 12.	Static characteristics: digital pins10
Table 13.	Static characteristics: analog I/O pins
	DP and DM12
Table 14.	Dynamic characteristics: analog I/O pins
	DP and DM12
Table 15.	Type A carrier tape dimensions for the
	ISP1102AW17
Table 16.	SnPb eutectic process (from J-STD-020C)19
Table 17.	Lead-free process (from J-STD-020C)19
Table 18.	Abbreviations
Table 19.	Revision history

continued >>

# **ISP1102A**

## 23. Figures

Fig 1.	Block diagram
Fig 2.	Pin configuration HBCC16 (top view)
Fig 3.	Human body ESD test model
Fig 4.	Rise time and fall time14
Fig 5.	Timing of VPO and VMO to DP and DM14
Fig 6.	Timing of OE_N to DP and DM14
Fig 7.	Timing of DP and DM to RCV, VP/VPO and
	VM/VMO14
Fig 8.	Load on pins DP and DM15
Fig 9.	Load on pins DP and DM for enable time and
	disable time
Fig 10.	Load on pins VM/VMO, VP/VPO and RCV 15
Fig 11.	Package outline SOT639-2 (HBCC16) 16
Fig 12.	Carrier tape dimensions
Fig 13.	Temperature profiles for large and small
	components

continued >>

# **ISP1102A**

## 24. Contents

1	General description	1
2	Features	1
3	Applications	2
4	Ordering information	2
5	Block diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	5
7.1	Function selection	5
7.2	Operating functions	5
7.3	Power supply configurations	5
7.4	Power supply input options	7
8	ElectroStatic Discharge (ESD)	8
8.1	ESD protection	8
8.2	ESD test conditions	8
9	Limiting values	9
10	Recommended operating conditions	9
11	Static characteristics	9
12	Dynamic characteristics 1	2
13	Test information 1	15
14	Package outline 1	6
15	Packing information	17
16	-	17
16.1		18
16.2	Ū Ū	18
16.3	-	8
16.4	Reflow soldering 1	8
17	Abbreviations 2	20
18	References 2	20
19	Revision history	20
20	Legal information	21
20.1	Data sheet status 2	21
20.2	Definitions 2	21
20.3	Disclaimers	
20.4	Trademarks2	
21	Contact information 2	21
22	Tables	22
23	Figures 2	23
24	Contents	24

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